TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER MMIC AMPLIFIER TMD0305-2

FEATURES

- HIGH POWER
 P1dB=33.0dBm at 3.4GHz to 5.1GHz
- HIGH GAIN
 G1dB=22.0dB at 3.4GHz to 5.1GHz
- BROAD BAND INTERNALLY MATCHED
- HERMETICALLY SEALED PACKAGE

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain Supply Voltage	VDD	V	15
Gate Supply Voltage	VGG	V	-10
Input Power	Pin	dBm	25
Flange Temperature	Tf	°C	-30 ~ + 80
Storage Temperature	Tstg	°C	-65 ~ + 175

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

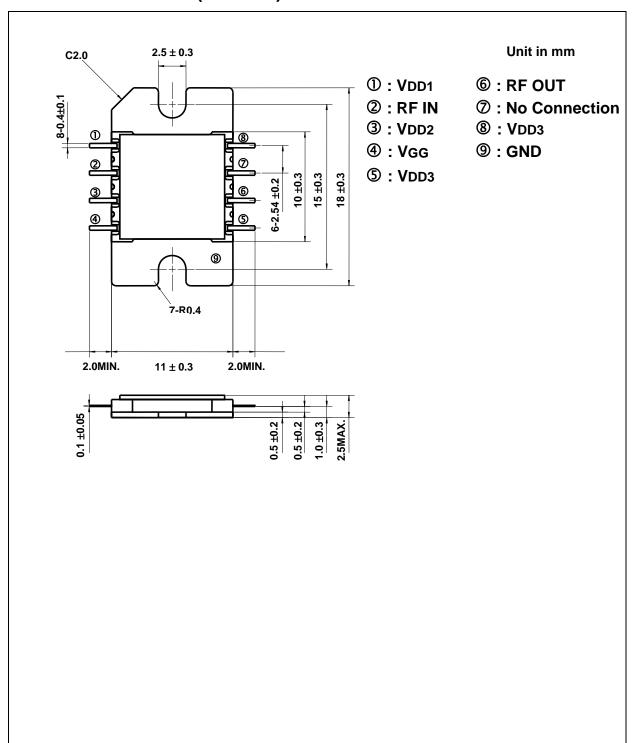
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain	P1dB		dBm	32.0	33.0	
Compression Point		VDD1=VDD2=VDD3				
Power Gain at 1dB Gain	G1dB	= 10V	dB	20.0	22.0	
Compression Point		VGG= -5V				
Drain Current*	IDD		Α		1.6	1.9
Input VSWR	VSWRin	f = 3.4 - 5.1GHz		_	_	3.0

^{*} IDD = IDD1 + IDD2 + IDD3

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PACKAGE OUTLINE (2-11E1A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C. Flanges of devices should be attached using screws and washers. Recommended torque is 0.18-0.20 N·m.